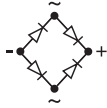
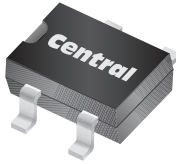


CBRSDSH2-100

SURFACE MOUNT SILICON
HIGH DENSITY
2.0 AMP
SCHOTTKY BRIDGE RECTIFIER

HD
BRIDGE



SMDIP CASE



www.centra-semi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRSDSH2-100 is a full wave bridge rectifier mounted in a durable epoxy surface mount case, utilizing glass passivated chips.

MARKING: FULL PART NUMBER

FEATURES:

- High 2.0A Current Rating
- Low V_F Schottky Diodes (700mV MAX @ $I_F=2.0A$)

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

Peak Repetitive Reverse Voltage

DC Blocking Voltage

RMS Reverse Voltage

Average Forward Current ($T_A=75^\circ\text{C}$)

Peak Forward Surge Current (8.3ms)

Operating Junction Temperature

Storage Temperature

SYMBOL

V_{RRM}

100

V_R

100

$V_{R(RMS)}$

70

I_O

2.0

I_{FSM}

110

T_J

-50 to +125

T_{stg}

-50 to +150

UNITS

V

V

V

A

A

$^\circ\text{C}$

$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL

TEST CONDITIONS

TYP

MAX

UNITS

I_R

$V_R=100V$

1.0

50

μA

V_F

$I_F=2.0A$

650

700

mV

C_J

$V_R=4.0V$, $f=1.0\text{MHz}$

280

500

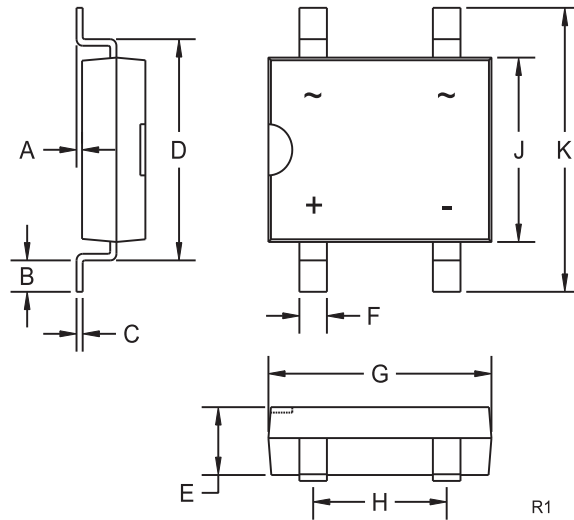
pF

CBRSDSH2-100

SURFACE MOUNT SILICON
HIGH DENSITY
2.0 AMP
SCHOTTKY BRIDGE RECTIFIER



SMDIP CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.008	0.10	0.20
B	0.040	0.060	1.02	1.52
C	0.009		0.23	
D	0.290	0.310	7.37	7.87
E	0.086	0.098	2.18	2.49
F	0.038	0.042	0.97	1.07
G	0.316	0.335	8.03	8.51
H	0.195	0.205	4.95	5.21
J	0.245	0.255	6.22	6.48
K	0.360	0.410	9.14	10.41

SMDIP (REV: R1)

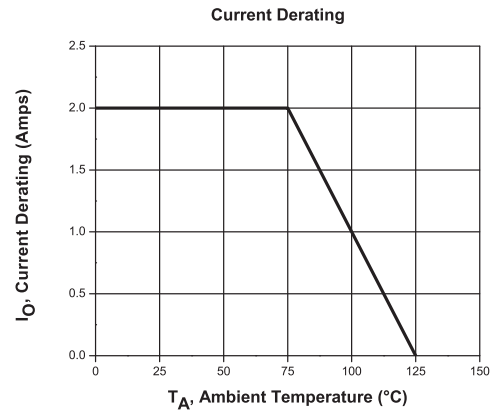
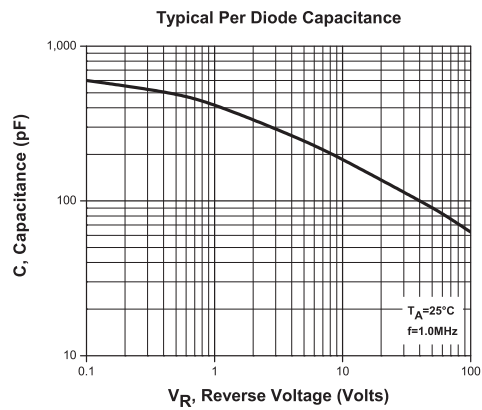
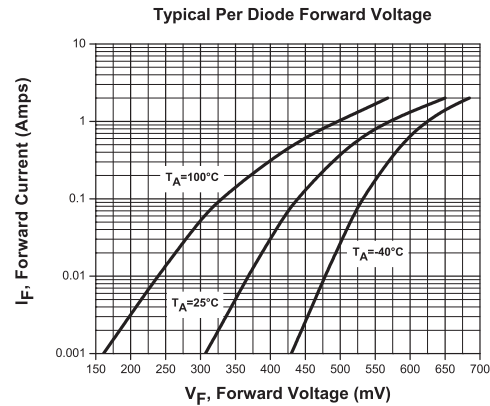
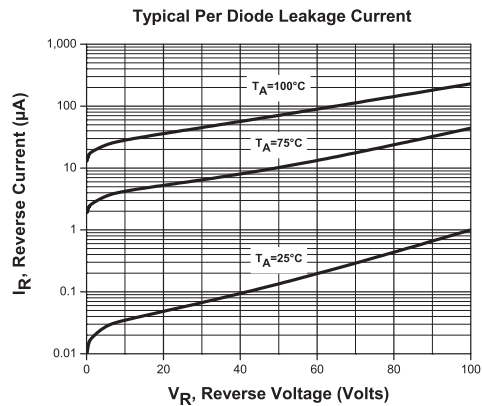
MARKING: FULL PART NUMBER

R3 (4-January 2013)

CBRSDSH2-100
SURFACE MOUNT SILICON
HIGH DENSITY
2.0 AMP
SCHOTTKY BRIDGE RECTIFIER



TYPICAL ELECTRICAL CHARACTERISTICS



R3 (4-January 2013)